

LOW POWER LINEAR AMPLIFIER

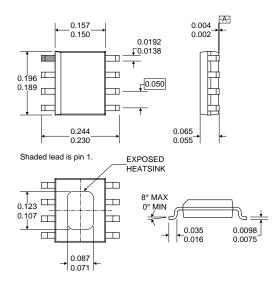
RoHS Compliant & Pb-Free Product

Typical Applications

- 2.14GHz UMTS Systems
- Digital Communication Systems
- PCS Communication Systems
- Commercial and Consumer Systems

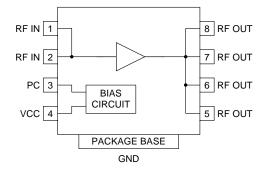
Product Description

The RF5187 is a highly-linear, low-power amplifier IC. It has been designed for use as the driver RF amplifier in applications such as W-CDMA basestations. The RF5187 requires an input and output matching network and power supply feed line. The device is manufactured on an advanced Gallium Arsenide HBT process, and is packaged in a 8-pin plastic package with a backside ground.



Package Style: SOIC-8 Slug

☐ InGaP/HBT ☐ GaN HEMT ☐ SiGe Bi-CMOS



Functional Block Diagram

Features

- Single 3V to 6V Supply
- 10dBm to 20dBm Ultra Linear Output Power
- 14dB Gain at 2.14GHz
- Power Down Mode
- 800MHz to 2500MHz Operation

Ordering Information

RF5187 Low Power Linear Amplifier RF5187PCBA-41X Fully Assembled Evaluation Board

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RF5187

Absolute Maximum Ratings

A to o to t					
Parameter	Rating	Unit			
Supply Voltage (V _{CC})	-0.5 to +6.5	V_{DC}			
Power Control Voltage (V _{PC})	-0.5 to +5 V	V			
DC Supply Current	300	mA			
Input RF Power	+20	dBm			
Output Load VSWR	20:1				
Operating Ambient Temperature	-40 to +85	°C			
Storage Temperature	-40 to +100	°C			



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Parameter	Specification		l lmi4	Condition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Overall					T=25°C, V _{CC} =5.0V, I _{CC} =240mA, Freq=2140MHz, P _{OUT} =13dBm	
Frequency Range	800		2500	MHz		
Output Power		13		dBm		
OP1dB		29		dBm		
Small Signal Gain	13		15	dB		
Input VSWR		1.5:1			With external matching network.	
Two-Tone Specification						
Output IP3	41	43	45	dBm	13dBm per tone.	
Power Control						
V_{PC}	2.7	3.1	3.7	V	To obtain 240mA idle current.	
Power Control "OFF"	0.2	0.5		V	Threshold voltage at device input.	
Power Supply						
Power Supply Voltage	5		6	V		
Supply Current			240	mA		
Power Down Current		2	10	μΑ	V _{PC} =0.2V	

Note: For infrastructure class operation, the maximum allowable current over all operating conditions is 260mA. This implies the need for an external active bias control network to control I_{CC} over temperature and normal process variation. A recommended active bias control circuit is included in the datasheet.

The maximum continuous allowable dissipated power ($I_{CC}^*V_{CC}^-P_{RF}$) for this part is 1.3W. For $V_{CC}^-=5.0$ V, this implies an I_{CC} limit of 260mA. A V_{CC} of 6.0V would have an I_{CC} limit of 215mA.

A constant I_{CC} of 180 mA to 220 mA provides an excellent combination of high linearity and low power dissipation. Refer to W-CDMA ACP curves at bottom of datasheet.

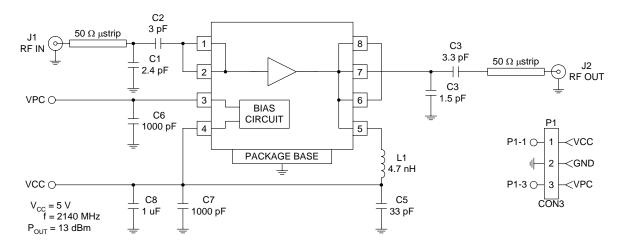
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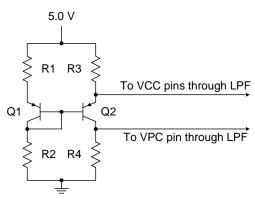
Pin	Function	Description	Interface Schematic
1	RF IN	RF input. This input is DC-coupled, so an external blocking capacitor is required if this pin is connected to a DC path. An optimum match to 50Ω is obtained by providing an external series capacitor of 2.4pF and then a shunt capacitor of 2.4pF. Those values are typical for 2140MHz; other values may be required for other frequencies.	
2	RF IN	Same as pin 1.	
3	PC	Power control pin. For obtaining maximum performance, the voltage on this pin can be used to set correct bias level. For low power linear applications, it is recommended that a constant bias control loop be used (see datasheet evaluation board schematic). A voltage of 0.5V or less at V_{PC} brings the part into Power Down State.	
4	VCC	Power supply pin for the bias circuits. External low frequency bypass capacitors should be connected if no other low frequency decoupling is nearby.	
5	RF OUT	RF output and bias for the output stage. The power supply for the output transistor needs to be supplied to this pin. This can be done through a quarter-wavelength microstrip line that is RF-grounded at the other end, or through an RF inductor that supports the required DC currents. Optimum load impedance is achieved by providing a shunt capacitor of 1.8pF and a series capacitor of 3.3pF. Those values are typical for 2140MHz; other values may be required for other frequencies. Since there are several output pins available (which are internally connected), one pin can be used for connecting the bias, another for connecting a (third) harmonic trap filter, and the other pins for the RF output.	
6	RF OUT	Same as pin 5.	
7	RF OUT	Same as pin 5.	
8	RF OUT	Same as pin 5.	
Pkg Base	GND	Ground connection. The backside of the package should be connected to the ground plane through a short path (i.e., vias under the device may be required).	

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Evaluation Board Schematic 2140MHz Operation



Constant Bias Circuit

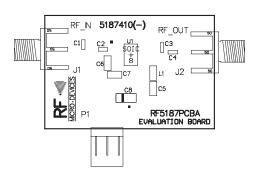


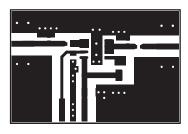
Bias Point	R1	R2	R3	R4
mA	Ω	Ω	Ω	Ω
100	120	1200	3.6	820
120	120	1200	3.0	820
150	120	1200	2.5	820
180	120	1200	2.0	820
200	120	1200	1.8	820
220	120	1200	1.7	820
240	120	1200	1.6	820

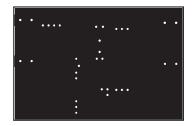
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Evaluation Board Layout Board Size 1.5" x 1.0"

Board Thickness 0.031", Board Material FR-4

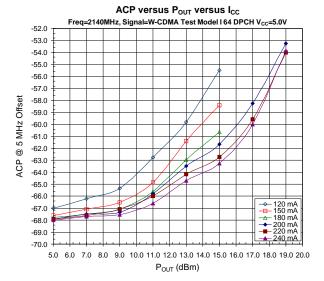






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